



Shantou Huashan Electronic Devices Co.,Ltd.

PNP SILICON TRANSISTOR

H1270

CENERAL PURPOSE APPLICATION.

SWITCHING APPLICATION

ABSOLUTE MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$)

T_{stg} —Storage Temperature..... $-55\sim 150^{\circ}\text{C}$

T_j —Junction Temperature..... 150°C

P_C —Collector Dissipation..... 500mW

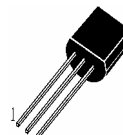
V_{CBO} —Collector-Base Voltage..... -35V

V_{CEO} —Collector-Emitter Voltage..... -30V

V_{EBO} —Emitter-Base Voltage..... -5V

I_C —Collector Current..... -500mA

TO-92



1—Emitter, E

2—Collector, C

3—Base, B

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
I_{CBO}	Collector Cut-off Current			-100	nA	$V_{\text{CB}}=-35\text{V}$, $I_{\text{E}}=0$
I_{EBO}	Emitter Cut-off Current			-100	nA	$V_{\text{EB}}=-5\text{V}$, $I_{\text{C}}=0$
$H_{\text{FE}}(1)$	DC Current Gain	70		240		$V_{\text{CE}}=-1\text{V}$, $I_{\text{C}}=-100\text{mA}$
$H_{\text{FE}}(2)$		25				$V_{\text{CE}}=-6\text{V}$, $I_{\text{C}}=-400\text{mA}$
$V_{\text{CE(sat)}}$	Collector- Emitter Saturation Voltage		-0. 1	-0. 25	V	$I_{\text{C}}=-100\text{mA}$, $I_{\text{B}}=-10\text{mA}$
V_{BE}	Base-Emitter Voltage		-0. 8	-1. 0	V	$I_{\text{C}}=-1\text{A}$, $I_{\text{B}}=-100\text{mA}$
f_{T}	Current Gain-Bandwidth Product		200		MHz	$V_{\text{CE}}=-6\text{V}$, $I_{\text{C}}=-20\text{mA}$
C_{ob}	Output Capacitance		13		pF	$V_{\text{CB}}=-6\text{V}$, $I_{\text{E}}=0$, $f=1\text{MHz}$

h_{FE} Classification

O

Y

70—140

120—240